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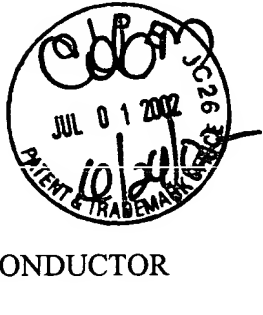
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Warwick

Application No.: 09/808,277

Filed: 03/14/2001

For: TRENCH-GATE SEMICONDUCTOR
DEVICES



Examiner: Rose, K.

Art Unit: 2822

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Commissioner for Patents
Washington D.C. 20231

AMENDMENT

Sir:

In response to the Office Action of March 25, 2002, Applicant hereby responds as follows:

IN THE CLAIMS

Please amend claims 1, 5, and 6 to appear as set forth below. A separate markup sheet accompanies this amendment. For clarity purposes, all claims are shown below.

1. (Amended) A trench-gate semiconductor device, comprising:

a semiconductor body having an active cell area wherein trenches containing gate material extend into the semiconductor body from a surface thereof, wherein adjacent to each trench-gate there is a source region at said semiconductor body surface separated from a drain region by a channel-accommodating body region, and wherein a source electrode contacts the

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